

60 V, N-channel Trench MOSFET

26 April 2019

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | 60 | V |
| V _{GS} | gate-source voltage | | | -20 | - | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | - | 1.8 | А |
| Static chara | octeristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 1.8 A; T _j = 25 °C | | - | 176 | 222 | mΩ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

nexperia

5. Pinning information

| Table 2. F | Pinning inf | formation | | |
|------------|-------------|-------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | D | drain | | D |
| 2 | D | drain | | |
| 3 | G | gate | | G ↓ ↓ ↓ ↓ |
| 4 | S | source | TSOP6 (SOT457) | |
| 5 | D | drain | | |
| 6 | D | drain | 1 | |
| | | | | 017aaa255 |

6. Ordering information

Table 3. Ordering information

| Type number Package | | | | |
|---------------------|-------|--|---------|--|
| | Name | Description | Version | |
| PMN230ENEA | TSOP6 | plastic surface-mounted package (TSOP6); 6 leads | SOT457 | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMN230ENEA | J6 |

8. Limiting values

Table 5. Limiting values

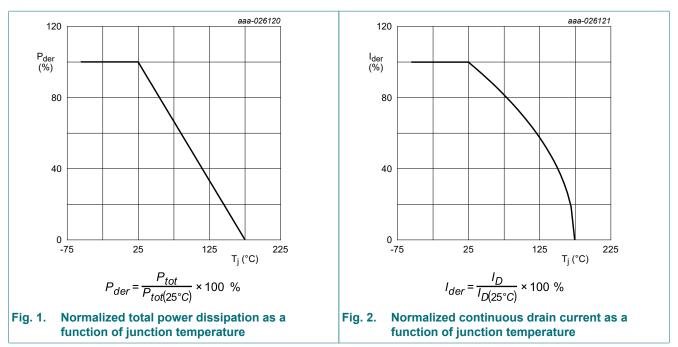
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|----------------------|--|--|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 60 | V |
| V _{GS} | gate-source voltage | _ | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | 1.8 | А |
| | | V _{GS} = 10 V; T _{amb} = 100 °C | [1] | - | 1.1 | А |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$ | | - | 7.1 | А |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 625 | mW |
| | | | [1] | - | 1.5 | W |
| | | T _{sp} = 25 °C | | - | 5.4 | W |
| Tj | junction temperature | | | -55 | 175 | °C |
| T _{amb} | ambient temperature | | | -55 | 175 | °C |
| T _{stg} | storage temperature | | | -65 | 175 | °C |
| Source-drain | n diode | | | | | |
| Is | source current | T _{amb} = 25 °C | [1] | - | 1.5 | А |
| ESD maximu | um rating | | | | | |
| V _{ESD} | electrostatic discharge voltage | НВМ | [3] | - | 2000 | V |
| Avalanche r | uggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | T _{j(init)} = 25 °C; I _D = 0.17 A; DUT in v avalanche (unclamped) | | - | 5 | mJ |
| | | 1 | | | | |

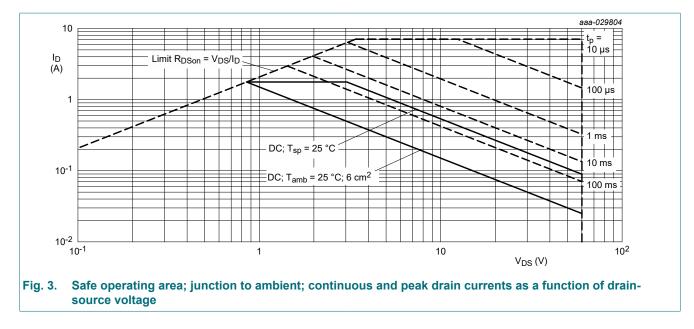
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



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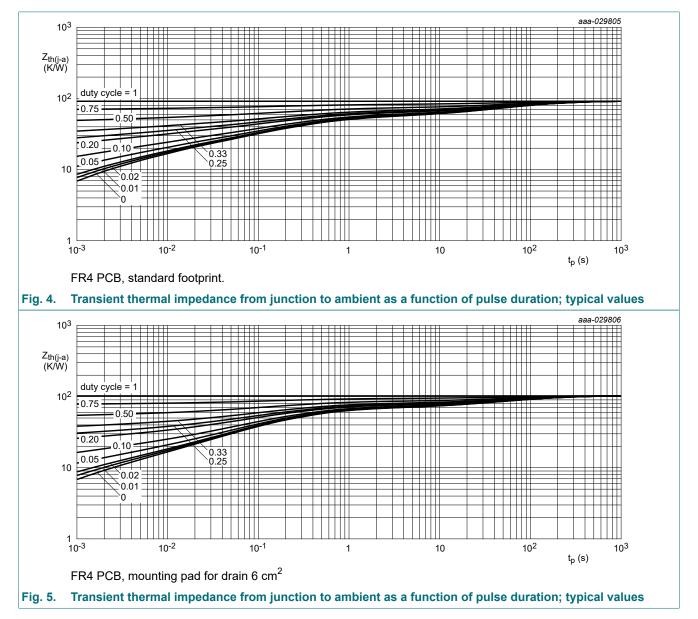


9. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|-----|------|
| ui(j-a) | thermal resistance from | in free air | [1] | - | 210 | 240 | K/W |
| | junction to ambient | | [2] | - | 90 | 100 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 22 | 28 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

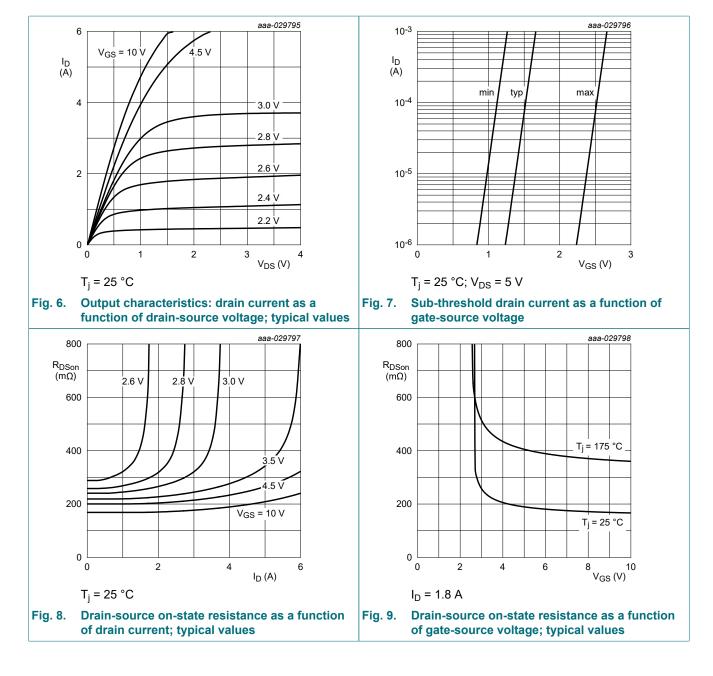


10. Characteristics

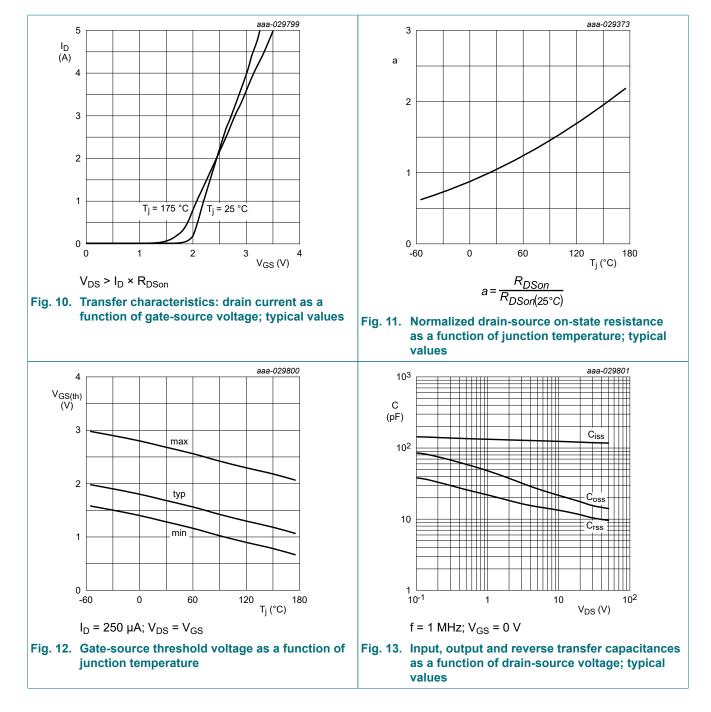
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|---|-----|------|-----|------|
| Static chara | octeristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 60 | - | - | V |
| V _{GSth} | gate-source threshold voltage | $I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$ | 1.3 | 1.7 | 2.7 | V |
| I _{DSS} | drain leakage current | V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μA |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -10 | μA |
| | | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 1 | μA |
| | | V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -1 | μA |
| R _{DSon} | drain-source on-state | V _{GS} = 10 V; I _D = 1.8 A; T _j = 25 °C | - | 176 | 222 | mΩ |
| | resistance | V _{GS} = 10 V; I _D = 1.8 A; T _j = 175 °C | - | 382 | 482 | mΩ |
| | | V _{GS} = 4.5 V; I _D = 1.6 A; T _j = 25 °C | - | 196 | 262 | mΩ |
| 9 _{fs} | forward transconductance | V _{DS} = 10 V; I _D = 2 A; T _j = 25 °C | - | 4 | - | S |
| R _G | gate resistance | f = 1 MHz | - | 13.2 | - | Ω |
| Dynamic ch | aracteristics | | | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = 30 V; I _D = 1.8 A; V _{GS} = 10 V; | - | 2.5 | 3.8 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.3 | - | nC |
| Q _{GD} | gate-drain charge | | - | 0.7 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V; | - | 110 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 16 | - | pF |
| C _{rss} | reverse transfer capacitance | - | - | 11 | - | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = 30 V; I _D = 1.8 A; V _{GS} = 10 V; | - | 2 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 5 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 7 | - | ns |
| t _f | fall time | | - | 3 | - | ns |
| Source-drai | n diode | · · | | | | |
| V _{SD} | source-drain voltage | I _S = 1.5 A; V _{GS} = 0 V; T _j = 25 °C | - | 0.8 | 1.2 | V |
| t _{rr} | reverse recovery time | I _S = 0.8 A; dI _S /dt = -100 A/µs; | - | 10 | - | ns |
| Q _r | recovered charge | V _{GS} = 0 V; V _{DS} = 30 V; T _j = 25 °C | - | 3 | - | nC |

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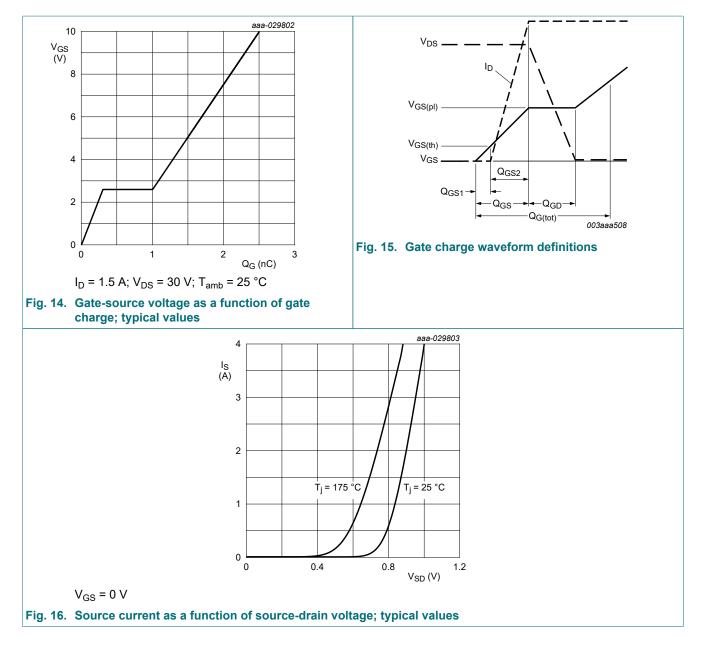
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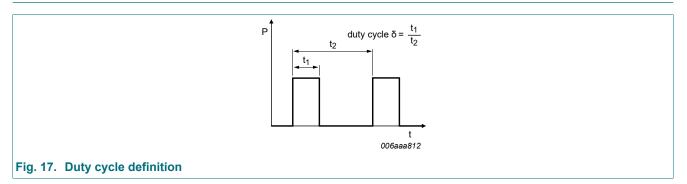


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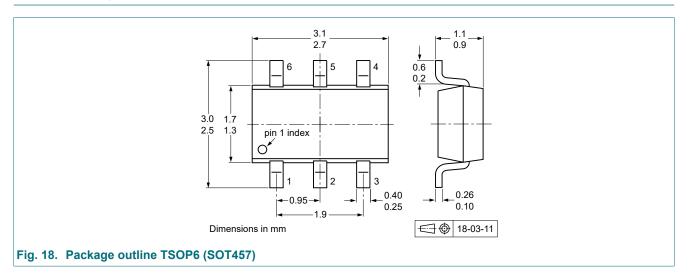
11. Test information



Quality information

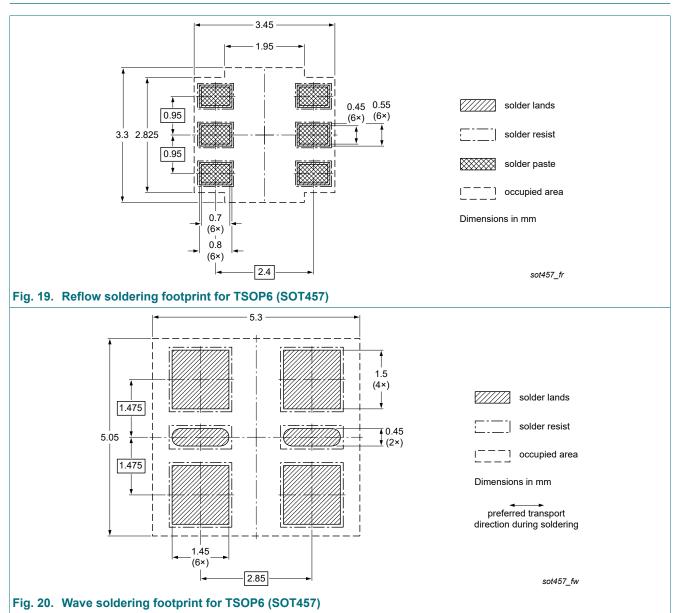
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



14. Revision history

| Table 8. Revision history | | | | | | |
|---------------------------|--------------|--------------------|---------------|------------|--|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | |
| PMN230ENEA v.1 | 20190426 | Product data sheet | - | - | | |

PMN230ENEA

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|-----------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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